Serial No. 10/808,059 Attorney Docket No. 400.285US01
Title: NROM MEMORY DEVICE WITH HIGH-PERMITTIVITY GATE DIELECTRIC FORMED BY THE

LOW TEMPERATURE OXIDIZATION OF METALS

AMENDMENTS TO THE SPECIFICATION

Please replace the original paragraph 25 with this replacement paragraph 25:

[0025] Embodiments of this category of oxide – nitride – high-k dielectric layers nanolaminates include: oxide – $\frac{\text{oxide nitride}}{\text{oxide}}$ – Al₂O₃ (where the Al is oxidized to form the Al₂O₃), oxide – $\frac{\text{oxide nitride}}{\text{oxide}}$ – HfO₂ (where the Hf is oxidized to form the HfO₂), and oxide – $\frac{\text{oxide nitride}}{\text{oxide}}$ – ZrO₂ (where the Zr is oxidized to form the ZrO₂). Alternate embodiments may include other dielectric materials.